

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Pravin K. Narwankar, et al.

Serial No. 10/772,893

Filed: February 4, 2004

For: Tailoring Nitrogen Profile In Silicon
Oxynitride Using Rapid Thermal
Annealing With Ammonia Under
Ultra-Low Pressure

) Examiner: Unassigned

) Art Unit: Unassigned

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

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Sir:

Enclosed is a copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 together with copies of the documents cited on that form, except for copies not required to be submitted (e.g., copies of U.S. patents and U.S. published patent applications need not be enclosed for applications filed after June 30, 2003). It is respectfully requested that the cited documents be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

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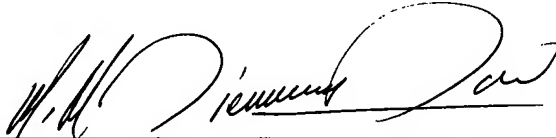
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Respectfully submitted,

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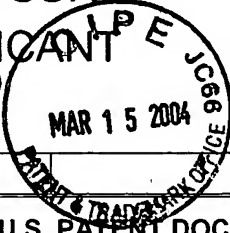
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Substitute for Form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete if Known	
			Application Number	10/772,893
			Filing Date	02/04/04
			First Named Inventor:	Pravin K. Narwankar
			Art Unit	Unassigned
			Examiner Name	Unassigned
			Attorney Docket Number	008209/USA/FEP/GCM/RKK
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Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		ITO, T., et al., "Direct Thermal Nitridation of Silicon Dioxide Films In Anhydrous Ammonia Gas," J. Electrochem Soc.: Solid-State and Technology/Optical Properties, Vol. 127, No. 9, September 1980, pages 2053-2057,	
		ITO, T., et al., "Retardation of Destructive Breakdown of SiO ₂ Films Annealed in Ammonia Gas," J. Electrochem Soc.: Solid-State and Technology/Ammonia Gas, Vol. 127, No. 10, September 1980, pages 2248-2251,	
		LEK, C. M., et al., "Impact of Decoupled Plasma Nitridation of Ultra-Thin Gate Oxide on the Performance of P-Channel MOSFETs," Institute of Physics Publishing, Semicond. Sci. Technol., Vol. 17, 2002, pages L25-L28.	

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